

IRF7422D2PbF

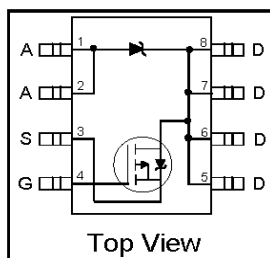
FETKY™ MOSFET & Schottky Diode

- Co-packaged HEXFET® Power MOSFET and Schottky Diode
- Ideal For Buck Regulator Applications
- P-Channel HEXFET
- Low V_F Schottky Rectifier
- Generation 5 Technology
- SO-8 Footprint
- Lead-Free

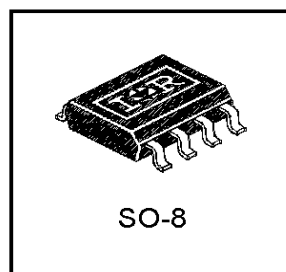
Description

The FETKY™ family of Co-packaged HEXFETs and Schottky diodes offer the designer an innovative board space saving solution for switching regulator and power management applications. Generation 5 HEXFETs utilize advanced processing techniques to achieve extremely low on-resistance per silicon area. Combining this technology with International Rectifier's low forward drop Schottky rectifiers results in an extremely efficient device suitable for use in a wide variety of portable electronics applications.

The SO-8 has been modified through a customized leadframe for enhanced thermal characteristics. The SO-8 package is designed for vapor phase, infrared or wave soldering techniques.



$V_{DSS} = -20V$
$R_{DS(on)} = 0.09\Omega$
Schottky $V_f = 0.52V$



Absolute Maximum Ratings

Parameter	Maximum	Units
$I_D @ T_A = 25^\circ C$	-4.3	A
$I_D @ T_A = 70^\circ C$	-3.4	
I_{DM}	-33	
$P_D @ T_A = 25^\circ C$	2.0	W
$P_D @ T_A = 70^\circ C$	1.3	
	16	mW/°C
V_{GS}	± 12	V
dv/dt	-5.0	V/ns
T_J, T_{STG}	-55 to +150	°C

Thermal Resistance Ratings

Parameter	Maximum	Units
$R_{\theta JA}$	62.5	°C/W

Notes:

- ① Repetitive rating – pulse width limited by max. junction temperature (see fig. 11)
- ② $I_{SD} \leq -2.2A$, $di/dt \leq -50A/\mu s$, $V_{DD} \leq V_{(BR)DSS}$, $T_J \leq 150^\circ C$
- ③ Pulse width $\leq 300\mu s$ – duty cycle $\leq 2\%$
- ④ Surface mounted on FR-4 board, $t \leq 10sec$.

MOSFET Electrical Characteristics @ $T_J = 25^\circ\text{C}$ (unless otherwise specified)

	Parameter	Min.	Typ.	Max.	Units	Conditions
$V_{(BR)DSS}$	Drain-to-Source Breakdown Voltage	-20	—	—	V	$V_{GS} = 0V, I_D = -250\mu A$
$R_{DS(on)}$	Static Drain-to-Source On-Resistance	—	0.07	0.09	Ω	$V_{GS} = -4.5V, I_D = -2.2A$ ③
		—	0.115	0.14		$V_{GS} = -2.7V, I_D = -1.8A$ ③
$V_{GS(th)}$	Gate Threshold Voltage	-0.70	—	—	V	$V_{DS} = V_{GS}, I_D = -250\mu A$
g_{fs}	Forward Transconductance	4.0	—	—	S	$V_{DS} = -16V, I_D = -2.2A$
I_{DSS}	Drain-to-Source Leakage Current	—	—	-1.0	μA	$V_{DS} = -16V, V_{GS} = 0V$
		—	—	-25		$V_{DS} = -16V, V_{GS} = 0V, T_J = 125^\circ\text{C}$
I_{GSS}	Gate-to-Source Forward Leakage	—	—	-100	nA	$V_{GS} = -12V$
	Gate-to-Source Reverse Leakage	—	—	100		$V_{GS} = 12V$
Q_g	Total Gate Charge	—	15	22	nC	$I_D = -2.2A$
Q_{gs}	Gate-to-Source Charge	—	2.2	3.3		$V_{DS} = -16V$
Q_{gd}	Gate-to-Drain ("Miller") Charge	—	6.0	9.0		$V_{GS} = -4.5V$, See Fig. 6 and 9 ③
$t_{d(on)}$	Turn-On Delay Time	—	8.4	—	ns	$V_{DD} = -10V$
t_r	Rise Time	—	26	—		$I_D = -2.2A$
$t_{d(off)}$	Turn-Off Delay Time	—	51	—		$R_G = 6.0\Omega$
t_f	Fall Time	—	33	—		$R_D = 4.5\Omega$, See Fig. 10 ③
C_{iss}	Input Capacitance	—	610	—	pF	$V_{GS} = 0V$
C_{oss}	Output Capacitance	—	310	—		$V_{DS} = -15V$
C_{rss}	Reverse Transfer Capacitance	—	170	—		$f = 1.0\text{MHz}$, See Fig. 5

MOSFET Source-Drain Ratings and Characteristics

	Parameter	Min.	Typ.	Max.	Units	Conditions
I_S	Continuous Source Current (Body Diode)	—	—	-2.5	A	
I_{SM}	Pulsed Source Current (Body Diode)	—	—	-17		
V_{SD}	Body Diode Forward Voltage	—	—	-1.0	V	$T_J = 25^\circ\text{C}, I_S = -1.8A, V_{GS} = 0V$
t_{rr}	Reverse Recovery Time (Body Diode)	—	56	84	ns	$T_J = 25^\circ\text{C}, I_F = -2.2A$
Q_{rr}	Reverse Recovery Charge	—	71	110	nC	$di/dt = -100A/\mu s$ ③

Schottky Diode Maximum Ratings

	Parameter	Max.	Units	Conditions
I_f (av)	Max. Average Forward Current	2.8	A	50% Duty Cycle. Rectangular Wave, $T_c = 25^\circ\text{C}$
		1.8		50% Duty Cycle. Rectangular Wave, $T_c = 70^\circ\text{C}$
I_{SM}	Max. peak one cycle Non-repetitive Surge current	200	A	5 μs sine or 3 μs Rect. pulse
		20		10ms sine or 6ms Rect. pulse

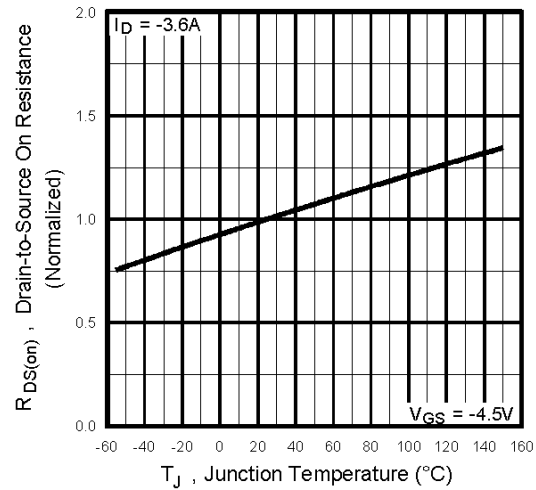
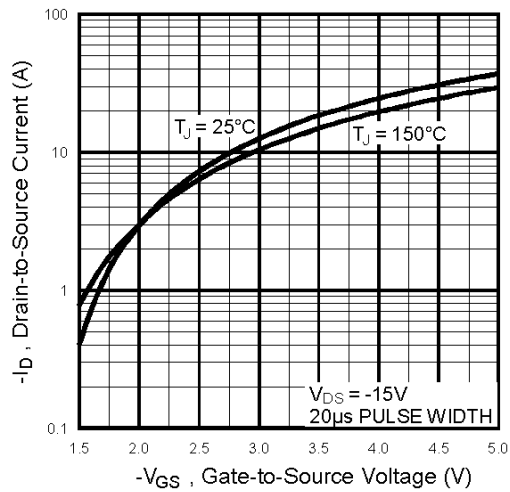
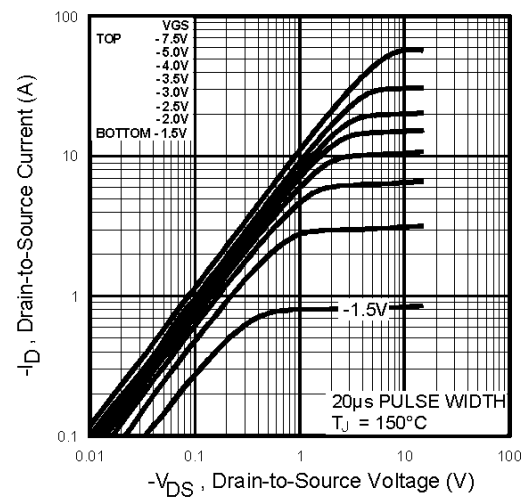
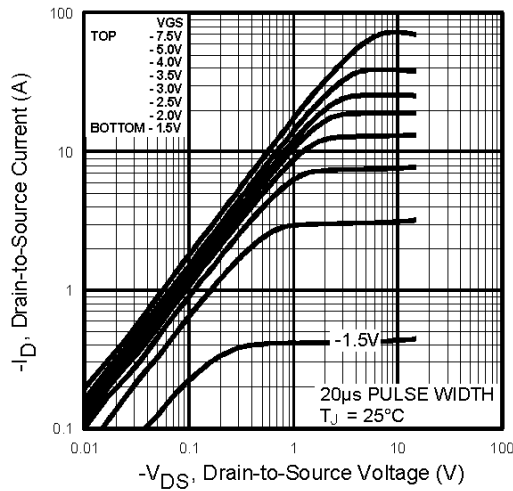
Following any rated load condition & with V_{rrm} applied

Schottky Diode Electrical Specifications

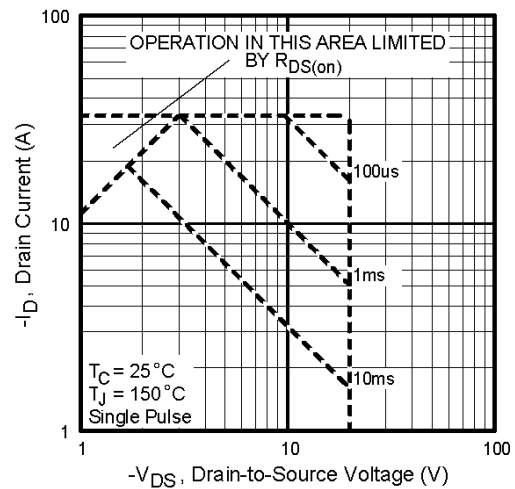
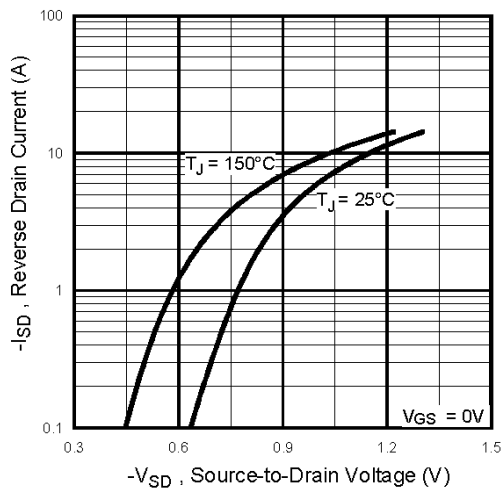
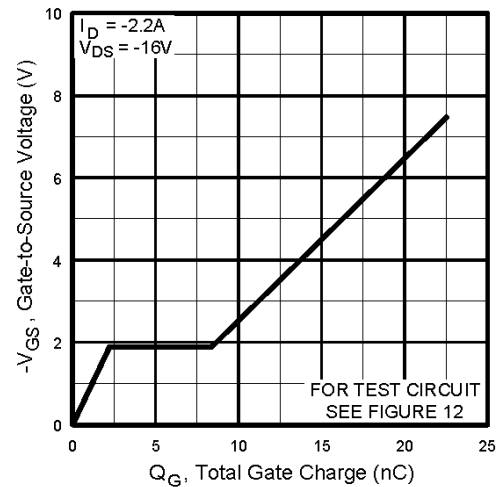
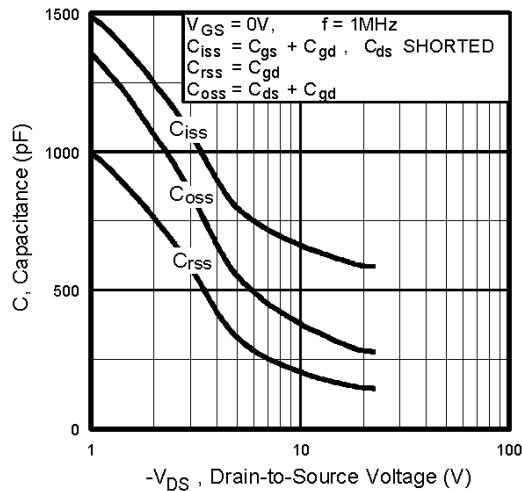
	Parameter	Max.	Units	Conditions
V_{fm}	Max. Forward voltage drop	0.57	V	$I_f = 3.0, T_J = 25^\circ\text{C}$
		0.77		$I_f = 6.0, T_J = 25^\circ\text{C}$
		0.52		$I_f = 3.0, T_J = 125^\circ\text{C}$
		0.79		$I_f = 6.0, T_J = 125^\circ\text{C}$
I_{rm}	Max. Reverse Leakage current	0.13	mA	$V_r = 20V, T_J = 25^\circ\text{C}$
		18		$T_J = 125^\circ\text{C}$
C_t	Max. Junction Capacitance	310	pF	$V_r = 5V_{dc}$ (100kHz to 1 MHz) 25°C
dv/dt	Max. Voltage Rate of Charge	4900	V/ μs	Rated V_r

(HEXFET is the reg. TM for International Rectifier Power MOSFET's)

Power Mosfet Characteristics



Power Mosfet Characteristics



Power Mosfet Characteristics

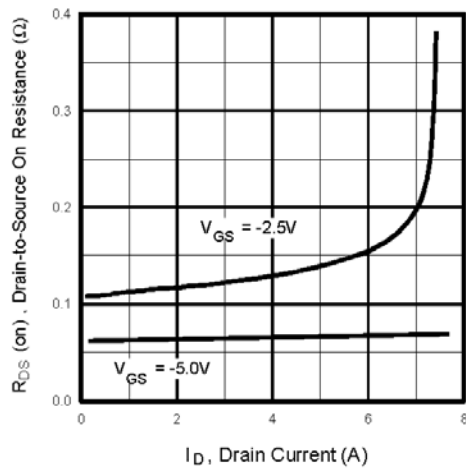
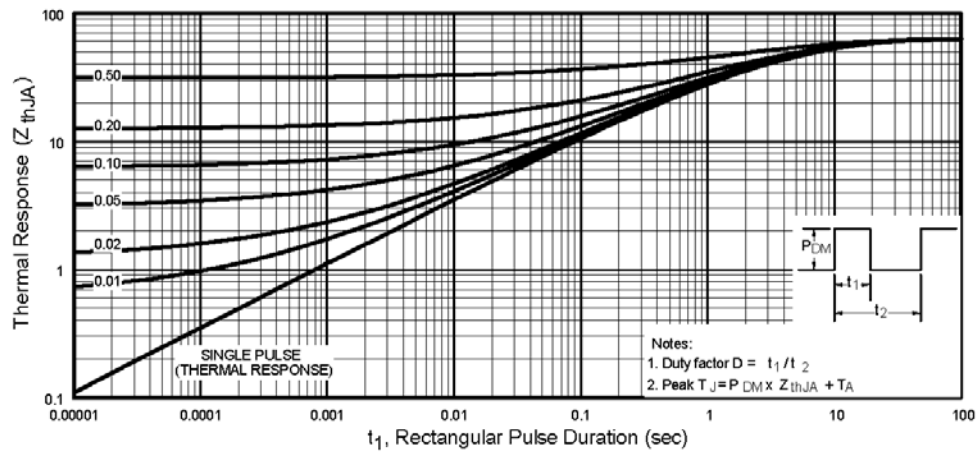


Fig 10. Typical On-Resistance Vs. Drain Current

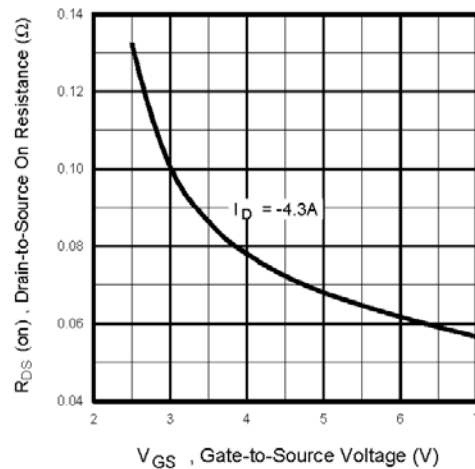


Fig 11. Typical On-Resistance Vs. Gate Voltage

Schottky Diode Characteristics

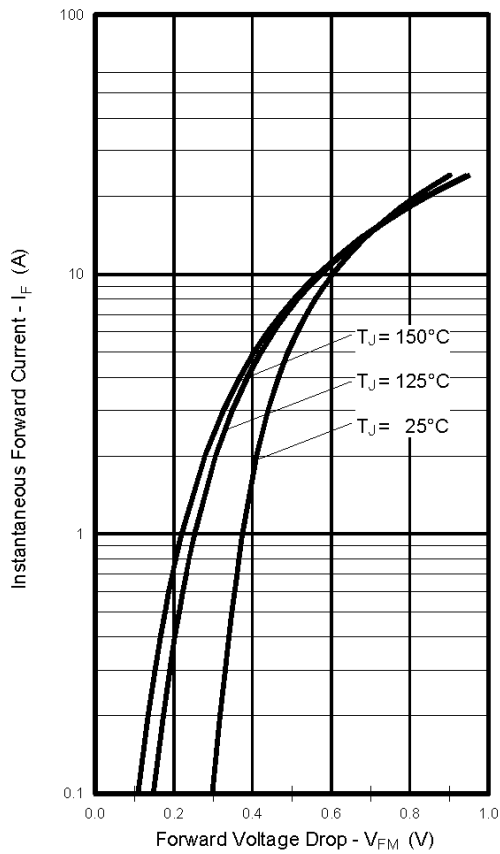


Fig. 12 - Typical Forward Voltage Drop Characteristics

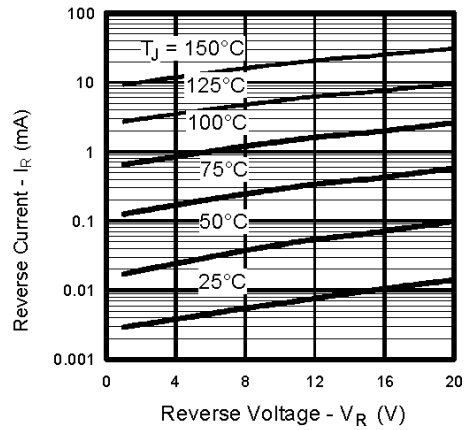


Fig. 13 - Typical Values of Reverse Current Vs. Reverse Voltage

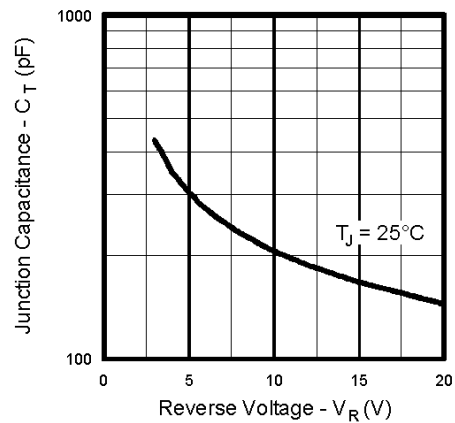
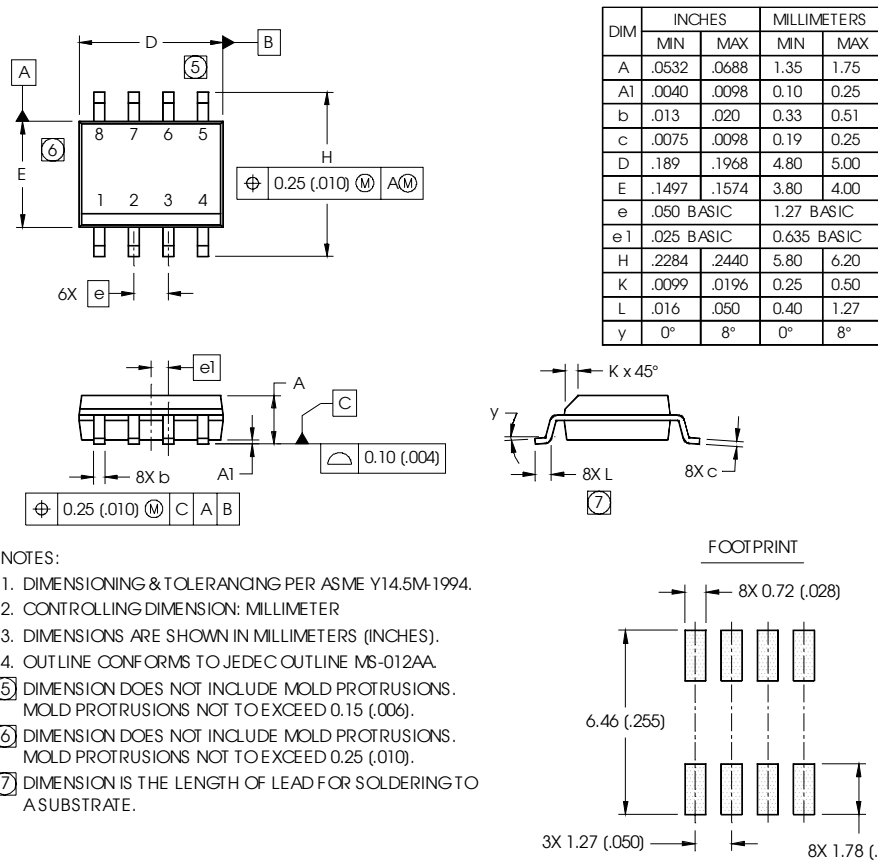


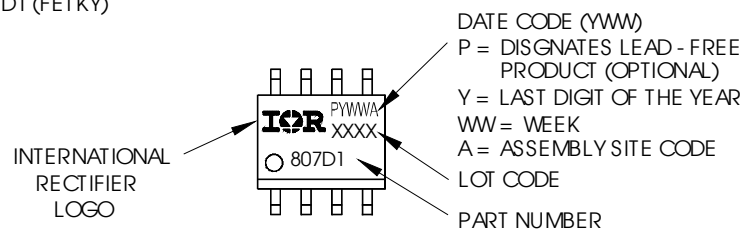
Fig. 14 - Typical Junction Capacitance Vs. Reverse Voltage

SO-8 (Fetky) Package Outline



SO-8 (Fetky) Part Marking Information

EXAMPLE: THIS IS AN IRF7807D1 (FETKY)

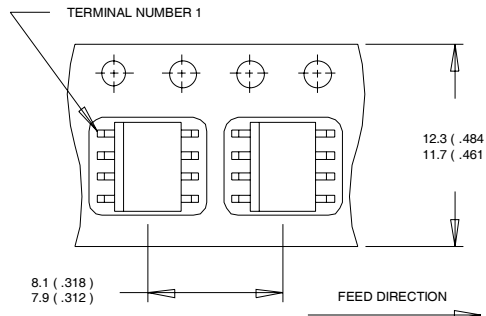


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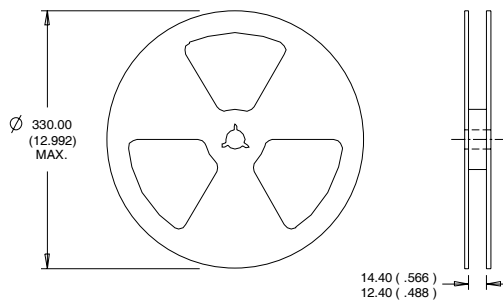
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SO-8 Tape and Reel

Dimensions are shown in millimeters (inches)



- NOTES:
1. CONTROLLING DIMENSION : MILLIMETER.
 2. ALL DIMENSIONS ARE SHOWN IN MILLIMETERS(INCHES).
 3. OUTLINE CONFORMS TO EIA-481 & EIA-541.



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1. CONTROLLING DIMENSION : MILLIMETER.
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Data and specifications subject to change without notice.
This product has been designed and qualified for the Consumer market.
Qualifications Standards can be found on IR's Web site.

International
IR Rectifier

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